

Fast switching diode chip in EMCON 3-Technology

FEATURES:

- 600V EMCON 3 technology 70 μm chip
- soft, fast switching
- low reverse recovery charge
- small temperature coefficient

This chip is used for:

- power module
- discrete components



Applications:

- drives
- white goods
- · resonant applications

| Chip Type | V_R | I _F | Die Size | Package |
|--------------|-------|----------------|--------------------------|--------------|
| SIDC06D60AC6 | 600V | 20A | 2.85 x 2 mm ² | sawn on foil |

MECHANICAL PARAMETER:

| MECHANICAE FARAMETER. | | | | |
|---------------------------------|---|-----------------|--|--|
| Raster size | 2.85 x 2 | | | |
| Area total / active | 5.70 / 3.86 | mm ² | | |
| Anode pad size | 2.43 x 1.58 | | | |
| Thickness | 70 | μm | | |
| Wafer size | 150 | mm | | |
| Flat position | 180 | deg | | |
| Max. possible chips per wafer | 2574 pcs | | | |
| Passivation frontside | Photoimide | | | |
| Anode metallization | 3200 nm AlSiCu | | | |
| Cathode metallization | Ni Ag –system suitable for epoxy and soft solder die bonding | | | |
| Die bond | electrically conductive glue or solder | | | |
| Wire bond | Al, ≤500μm | | | |
| Reject ink dot size | Ø 0.65mm; max 1.2mm | | | |
| Recommended storage environment | store in original container, in dry nitrogen, < 6 month at an ambient temperature of 23°C | | | |



Maximum Ratings

| Parameter | Symbol | Condition | Value | Unit |
|--|----------------------------|-----------|---------|------|
| Repetitive peak reverse voltage | V_{RRM} | | 600 | V |
| Continuous forward current limited by | 1_ | | 1) | - A |
| T _{jmax} | I _F | | | |
| Maximum repetitive forward current | 1 | | 40 | |
| limited by T _{jmax} | / FRM | | 40 | |
| Operating junction and storage temperature | $T_{\rm j}$, $T_{ m stg}$ | | -40+175 | °C |

¹⁾ depending on thermal properties of assembly

Static Electrical Characteristics (tested on chip), T_i =25 °C, unless otherwise specified

| Parameter | Symbol | Cond | Value | | | Unit | |
|------------------------------------|-----------------|-------------------------|------------------------------------|------|------|------|------|
| raiailletei | Syllibol | Cona | itions | min. | Тур. | max. | Onne |
| Reverse leakage current | I _R | V _R = 600 V | <i>T_j</i> =25° <i>C</i> | | | 27 | μΑ |
| Cathode-Anode breakdown Voltage | V _{Br} | I _R = 0.25mA | $T_j=25^{\circ}C$ | 600 | | | V |
| Forward voltage drop | V_{F} | I _F =20A | $T_j=25^{\circ}C$ | 1.25 | 1.6 | 1.95 | V |

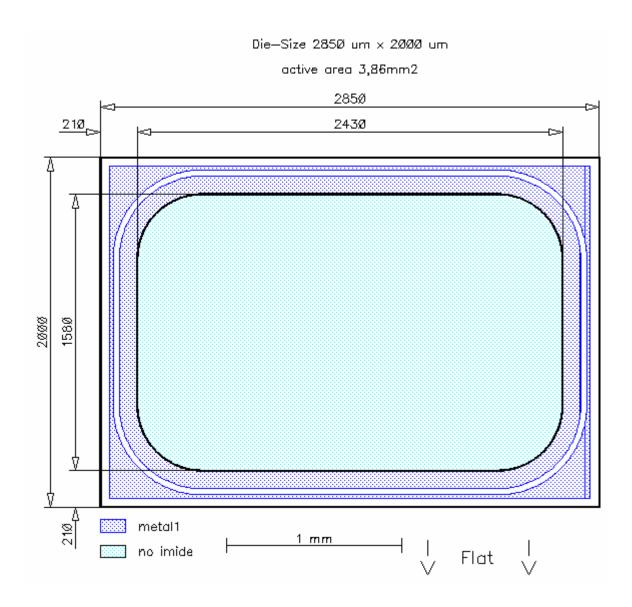
Dynamic Electrical Characteristics (verified by design/characterization), inductive load

| Parameter | Symbol | Conditions | | Value 2) | | | Unit |
|-------------------------------|------------------|---|---|----------|----------------------|------|------|
| raiailletei | Syllibol | | | min. | Тур. | max. | |
| Peak reverse recovery current | I _{RM} | $I_F=20A$ $di/dt=1800A/\mu s$ $V_R=300V$ $V_{GE}=-15V$ | $T_j = 25 ^{\circ}C$ $T_j = 125 ^{\circ}C$ $T_j = 150 ^{\circ}C$ | | 30.0 32.0 34.0 | | A |
| Recovered charge | Q _r | $I_F=20A$ $di/dt=1800A/\mu s$ $V_R=300V$ $V_{GE}=-15V$ | $T_j = 25 ^{\circ}C$ $T_j = 125 ^{\circ}C$ $T_j = 150 ^{\circ}C$ | | 1.00 1.75 2.20 | | μC |
| Reverse recovery energy | E _{rec} | $I_F=20A$ $di/dt=1800A/\mu s$ $V_R=300V$ $V_{GE}=-15V$ | $T_j = 25 ^{\circ}C$ $T_j = 125 ^{\circ}C$ $T_j = 150 ^{\circ}C$ | | 0.21 0.37 0.47 | | mJ |

²⁾ values also influenced by parasitic L- and C- in measurement and package.



CHIP DRAWING:





This chip data sheet refers to the device data sheet Description: AQL 0,65 for visual inspection according to failure catalog Electrostatic Discharge Sensitive Device according to MIL-STD 883 Test-Normen Villach/Prüffeld

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